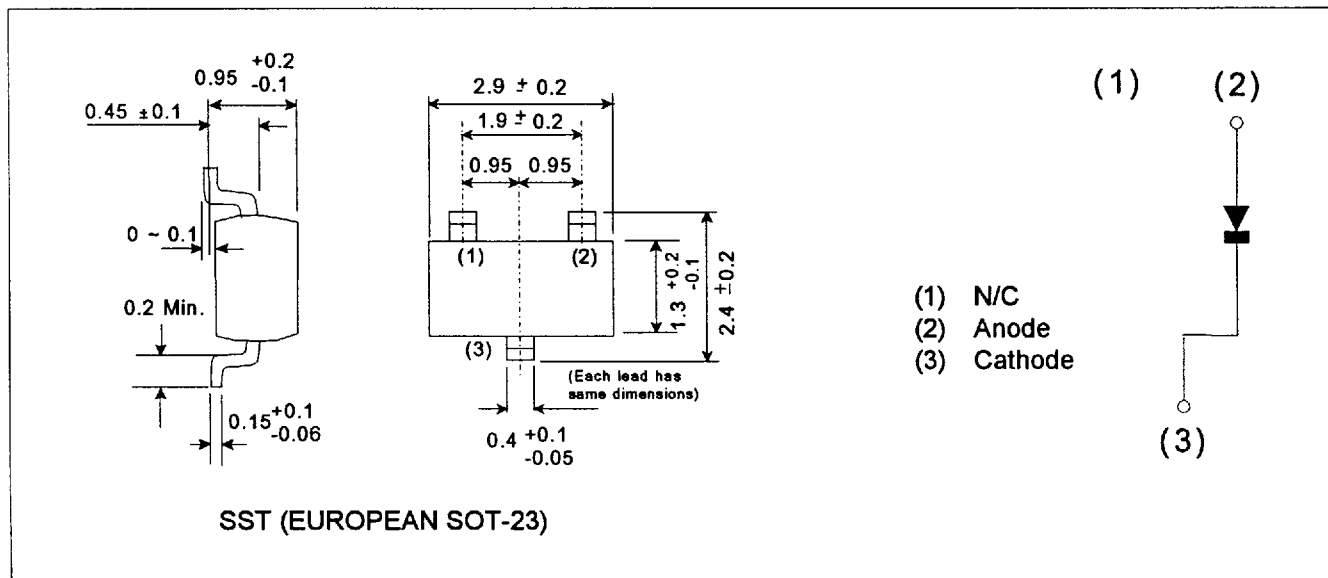


ROHM
SEMICONDUCTORS
DAN212C
SWITCHING DIODE : SOT-23
ABSOLUTE MAXIMUM RATINGS: (TA=25°C)

DC reverse voltage	V_R	100V
Peak reverse voltage	V_{RM}	100V
Average rectified current	I_O	100mA
Peak forward current	I_{FM}	300 mA
Surge current (1 μ s)	I_{surge}	4A
Power dissipation (mounted)	P_d	300mW
Junction temperature	T_j	150°C
Storage temperature range	T_{stg}	-55 ~ 150°C
Rated input/output frequency	f	100 MHz

ELECTRICAL CHARACTERISTICS: (Ta = 25°C, Unless Otherwise Specified)

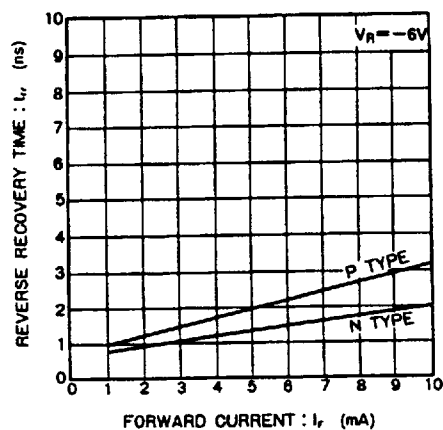
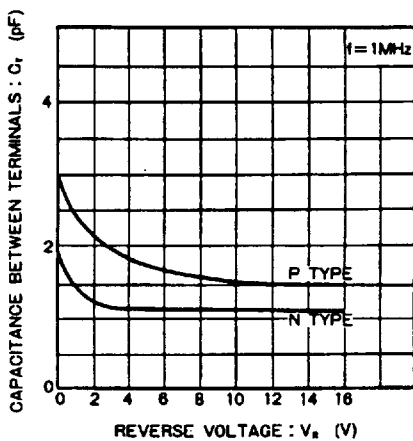
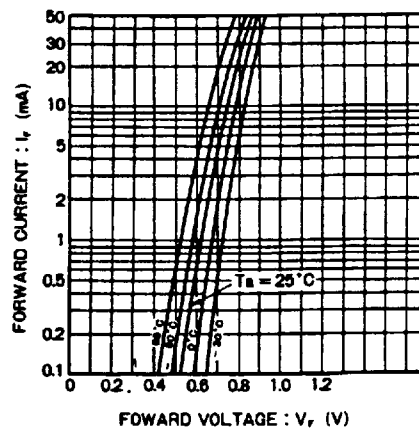
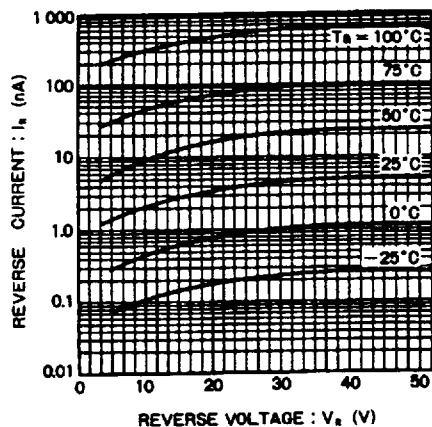
Parameter	Test Condition	Min.	Typ.	Max.	Unit
BV_R	$I_R = 100 \mu A$	100	145	-	V
I_R	$V_R = 20 V$	-	7	25	nA
I_R	$V_R = 20 V, T_A = 150^\circ C$	-	1.5	50	μA
I_R	$V_R = 80 V$	-	15	500	nA
V_F	$I_F = 10 mA$	-	0.73	1.0	V
V_F	$I_F = 50 mA$	-	0.85	1.1	V
V_F	$I_F = 100 mA$	-	0.93	1.2	V
C_T	$V_R = 0 V, f = 1.0 MHz$	-	2.25	4.0	pF
C_T	$V_R = 6 V, f = 1.0 MHz$	-	1.30	3.5	pF
t_{rr}	$V_R = 6 V, I_F = 10 mA, R_L = 50 Ohms$	-	2.0	4.0	ns

DIMENSIONS: (Unit mm)


Packaging Availability: T116 = 3,000 pc/reel
T216 = 10,000 pc/reel

COMMON CATHODE SWITCHING DIODE ARRAY

DAN212C



Note: P Type (DAP Devices)
N Type (DAN Devices)

